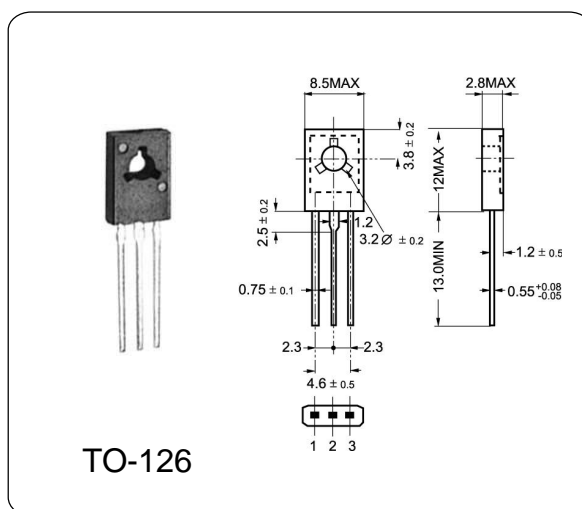


DESCRIPTION

It is intended for use in power amplifier and switching applications.

ABSOLUTE MAXIMUM RATINGS (Ta = 25 °C)

Parameter	I	Value	Unit
Collector-Base Voltage	V_{CBO}	80	V
Collector-Emitter Voltage	V_{CEO}	80	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	1.5	A
Base Current	I_B	0.5	A
Total Dissipation at	P_{tot}	12.5	W
Max. Operating Junction Temperature	T_j	150	°C
Storage Temperature	T_{stg}	-55~150	°C



ELECTRICAL CHARACTERISTICS (Ta = 25 °C)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Collector Cut-off Current	I_{CEO}	$V_{CB}=80V, I_E=0$	—	—	10	uA
Emitter Cut-off Current	I_{EBO}	$V_{EB}=5V, I_C=0$	—	—	10	uA
Collector-Emitter Sustaining Voltage	V_{CEO}	$I_C=30mA, I_B=0$	80	—	—	V
DC Current Gain	$h_{FE(1)}$	$V_{CE}=2V, I_C=0.5A$	25	—	—	
	$h_{FE(2)}$	$V_{CE}=2V, I_C=150mA$	40	—	250	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=0.5A, I_B=50mA$	—	—	0.5	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$V_{CE}=2V, I_C=0.5A$	—	—	1.0	V
Current Gain Bandwidth Product	f_T	$V_{CE}=10V, I_C=500mA$	3	—	—	MHz